Toshio Kamiya

List of Publications by Year in Descending Order

401 papers	30,416 citations	78 h-index	168 g-index
441 ext. papers	32,998 ext. citations	4 avg, IF	7.07 L-index

#	Paper	IF	Citations
401	Degenerated Hole Doping and Ultra-Low Lattice Thermal Conductivity in Polycrystalline SnSe by Nonequilibrium Isovalent Te Substitution.. *Advanced Science*, **2022**, e2105958	13.6	1
400	Defects and Relevant Properties **2022**, 93-103		
399	State and Role of Hydrogen in Amorphous Oxide Semiconductors **2022**, 145-157		1
398	Rare Earth and Transition Metal Doped Amorphous Oxide Semiconductor Phosphors for Novel Light-Emitting Diode Displays **2022**, 577-584		
397	Breaking of Thermopower-Conductivity Trade-Off in LaTiO Film around Mott Insulator to Metal Transition. *Advanced Science*, **2021**, 8, e2102097	13.6	2
396	Reversible 3D-2D structural phase transition and giant electronic modulation in nonequilibrium alloy semiconductor, lead-tin-selenide. *Science Advances*, **2021**, 7,	14.3	3
395	Local Structure Properties of Hydrogenated and Nonhydrogenated Amorphous InGaZnO Thin Films Using XAFS and High-Energy XRD. *Journal of Physical Chemistry C*, **2021**, 125, 13619-13628	3.8	
394	Double Charge Polarity Switching in Sb-Doped SnSe with Switchable Substitution Sites. *Advanced Functional Materials*, **2021**, 31, 2008092	15.6	5
393	15.1: Invited Paper: Understanding and controlling electronic defects in amorphous oxide semiconductor. *Digest of Technical Papers SID International Symposium*, **2021**, 52, 97-99	0.5	
392	Ion Substitution Effect on Defect Formation in Two-Dimensional Transition Metal Nitride Semiconductors, TiN (= Ca, Sr, and Ba). *Inorganic Chemistry*, **2021**, 60, 10227-10234	5.1	0
391	p-Type Transparent Quadruple Perovskite Halide Conductors: Fact or Fiction?. *Advanced Functional Materials*, **2020**, 30, 1909906	15.6	11
390	Phonon scattering limited mobility in the representative cubic perovskite semiconductors SrGeO3, BaSnO3, and SrTiO3. *Physical Review B*, **2020**, 101,	3.3	4
389	Study of the Electronic State of Hydrogen by a Combination of the Muon as Pseudo Hydrogen and First-Principles Calculation. *Journal of Computer Chemistry Japan*, **2020**, 19, 106-114	0.2	
388	Shallow Valence Band of Rutile GeO2 and P-type Doping. *Journal of Physical Chemistry C*, **2020**, 124, 25721-25728	3.6	8
387	Strain Engineering at Heterointerfaces: Application to an Iron Pnictide Superconductor, Cobalt-Doped BaFeAs. *ACS Applied Materials & Interfaces*, **2020**, 12, 50096-50104	9.5	2
386	Symmetric Ambipolar Thin-Film Transistors and High-Gain CMOS-like Inverters Using Environmentally Friendly Copper Nitride. *ACS Applied Materials & Interfaces*, **2019**, 11, 35132-35137	9.5	7
385	New Amorphous InGaZnO Thin-Film Transistor-Based Optical Pixel Sensor for Optical Input Signal With Short Wavelength. *IEEE Transactions on Electron Devices*, **2019**, 66, 3841-3846	2.9	1

384	Electronic structure of interstitial hydrogen in In-Ga-Zn-O semiconductor simulated by muon. *Applied Physics Letters*, **2019**, 115, 122104	3.4	11
383	Crystal Structure Built from a GeO6/GeO5 Polyhedra Network with High Thermal Stability: SrGe2O5. *ACS Applied Electronic Materials*, **2019**, 1, 1989-1993	4	2
382	Insulator-like behavior coexisting with metallic electronic structure in strained FeSe thin films grown by molecular beam epitaxy. *Physical Review B*, **2019**, 99,	3.3	3
381	Particulate Generation on Surface of Iron Selenide Films by Air Exposure. *Journal of Superconductivity and Novel Magnetism*, **2019**, 32, 3047-3055	1.5	3
380	Electronic Defects in Amorphous Oxide Semiconductors: A Review. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1800372	1.6	103
379	Transition Metal-Doped Amorphous Oxide Semiconductor Thin-Film Phosphor, Chromium-Doped Amorphous Gallium Oxide. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1800198	1.6	4
378	On the Origin of the Negative Thermal Expansion Behavior of YCu. *Inorganic Chemistry*, **2019**, 58, 11819-11827	3.1	
377	Intrinsic and Extrinsic Defects in Layered Nitride Semiconductor SrTiN2. *Journal of Physical Chemistry C*, **2019**, 123, 19307-19314	3.8	5
376	Amorphous Oxide Semiconductor Thin-Film Transistors **2019**, 573-587		3
375	Exotic Crystal Structures and Electronic Structures in Novel Structured Inorganic Materials **2019**, 107-120		
374	Multiple Color Inorganic Thin-Film Phosphor, RE-Doped Amorphous Gallium Oxide (RE = Rare Earth: Pr, Sm, Tb, and Dy), Deposited at Room Temperature. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1700833	1.6	11
373	Effects of Base Pressure on Growth and Optoelectronic Properties of Amorphous In-Ga-Zn-O: Ultralow Optimum Oxygen Supply and Bandgap Widening. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1700832	1.6	11
372	Multiple states and roles of hydrogen in p-type SnS semiconductors. *Physical Chemistry Chemical Physics*, **2018**, 20, 20952-20956	3.6	6
371	Bandgap Optimization of Perovskite Semiconductors for Photovoltaic Applications. *Chemistry - A European Journal*, **2018**, 24, 2305-2316	4.8	76
370	49.2: Invited Paper: Research and Applications of Amorphous Metal-Oxide Semiconductor Devices - In-Ga-Zn-O and Ga-Sn-O Thin-Film Devices -. *Digest of Technical Papers SID International Symposium*, **2018**, 49, 512-515	0.5	
369	Multiple Roles of Hydrogen Treatments in Amorphous InGaZnO Films. *ECS Journal of Solid State Science and Technology*, **2017**, 6, P365-P372	2	19
368	The Unique Electronic Structure of Mg Si: Shaping the Conduction Bands of Semiconductors with Multicenter Bonding. *Angewandte Chemie - International Edition*, **2017**, 56, 10135-10139	16.4	13
367	The Unique Electronic Structure of Mg2Si: Shaping the Conduction Bands of Semiconductors with Multicenter Bonding. *Angewandte Chemie*, **2017**, 129, 10269-10273	3.6	3

366	Amorphous Gallium Oxide as an Improved Host for Inorganic Light-Emitting Thin Film Semiconductor Fabricated at Room Temperature on Glass. *ECS Journal of Solid State Science and Technology*, **2017**, 6, P410-P414	2	6
365	Conversion of an ultra-wide bandgap amorphous oxide insulator to a semiconductor. *NPG Asia Materials*, **2017**, 9, e359-e359	10.3	56
364	Effects of working pressure and annealing on bulk density and nanopore structures in amorphous InGaZnO thin-film transistors. *Japanese Journal of Applied Physics*, **2017**, 56, 03BB03	1.4	9
363	BaFe2(As1−xPx)2(x= 0.22–0.42) thin films grown on practical metal-tape substrates and their critical current densities. *Superconductor Science and Technology*, **2017**, 30, 044003	3.1	9
362	Transparent amorphous oxide semiconductors for organic electronics: Application to inverted OLEDs. *Proceedings of the National Academy of Sciences of the United States of America*, **2017**, 114, 233-238	11.5	86
361	Key Factors for Insulator–Superconductor Transition in FeSe Thin Films by Electric Field. *IEEE Transactions on Applied Superconductivity*, **2017**, 27, 1-5	1.8	10
360	Electride and superconductivity behaviors in Mn5Si3-type intermetallics. *Npj Quantum Materials*, **2017**, 2,	5	28
359	P-13: Quantitative Analysis and Deconvolution of Subgap States in Amorphous In-Ga-Zn-O. *Digest of Technical Papers SID International Symposium*, **2017**, 48, 1273-1275	0.5	1
358	P-187: Electronic Structures of Various Color Light-Emitting Amorphous Oxide Semiconductor Thin Films. *Digest of Technical Papers SID International Symposium*, **2017**, 48, 1974-1976	0.5	2
357	An Exceptionally Narrow Band-Gap (~4 eV) Silicate Predicted in the Cubic Perovskite Structure: BaSiO. *Inorganic Chemistry*, **2017**, 56, 10535-10542	5.1	12
356	Electron effective mass and mobility limits in degenerate perovskite stannate BaSnO3. *Physical Review B*, **2017**, 95,	3.3	33
355	Transparent amorphous oxide semiconductor thin film phosphor, In–Mg–O:Eu. *Journal of the Ceramic Society of Japan*, **2016**, 124, 532-535	1	9
354	Enhanced critical-current in P-doped BaFeAs thin films on metal substrates arising from poorly aligned grain boundaries. *Scientific Reports*, **2016**, 6, 36828	4.9	26
353	Difficulty of carrier generation in orthorhombic PbO. *Journal of Applied Physics*, **2016**, 119, 165701	2.5	9
352	Ultrawide band gap amorphous oxide semiconductor, GaZnO. *Thin Solid Films*, **2016**, 614, 84-89	2.2	12
351	Effects of thermal annealing on elimination of deep defects in amorphous InGaZnO thin-film transistors. *Thin Solid Films*, **2016**, 614, 73-78	2.2	11
350	Electric field-induced superconducting transition of insulating FeSe thin film at 35 K. *Proceedings of the National Academy of Sciences of the United States of America*, **2016**, 113, 3986-90	11.5	73
349	Oxide TFTs **2016**, 1111-1144		7

348	69-4: NBIS-Stable Oxide Thin-Film Transistors Using Ultra-Wide Bandgap Amorphous Oxide Semiconductors. *Digest of Technical Papers SID International Symposium*, **2016**, 47, 951-953	0.5	6
347	31-4: Novel Inorganic Electron Injection and Transport Materials Enabling Large-Sized Inverted OLEDs Driven by Oxide TFTs. *Digest of Technical Papers SID International Symposium*, **2016**, 47, 401-404	0.5	2
346	Room-temperature fabrication of light-emitting thin films based on amorphous oxide semiconductor. *AIP Advances*, **2016**, 6, 015106	1.5	10
345	Amorphous pnictide semiconductor BaZn2As2 exhibiting high hole mobility. *Applied Physics Letters*, **2016**, 109, 242105	3.4	1
344	Solid phase epitaxial growth of high mobility La:BaSnO3 thin films co-doped with interstitial hydrogen. *Applied Physics Letters*, **2016**, 108, 172101	3.4	27
343	SnS thin films prepared by H2S-free process and its p-type thin film transistor. *AIP Advances*, **2016**, 6, 015112	1.5	11
342	Nonequilibrium Rock-Salt-Type Pb-Doped SnSe with High Carrier Mobilities □300 cm2/(Vs). *Chemistry of Materials*, **2016**, 28, 2278-2286	9.6	13
341	N-type conduction in SnS by anion substitution with Cl. *Applied Physics Express*, **2016**, 9, 051201	2.4	16
340	Widely bandgap tunable amorphous Cd□a□ oxide semiconductors exhibiting electron mobilities □10 cm2 V□1 s□1. *Applied Physics Letters*, **2015**, 106, 082106	3.4	13
339	Effects of Pb Doping on Hole Transport Properties and Thin-Film Transistor Characteristics of SnO Thin Films. *ECS Journal of Solid State Science and Technology*, **2015**, 4, Q26-Q30	2	17
338	n-type conversion of SnS by isovalent ion substitution: Geometrical doping as a new doping route. *Scientific Reports*, **2015**, 5, 10428	4.9	44
337	Vortex Pinning Properties of Phosphorous-Doped $hbox{BaFe}_{2}hbox{As}_{2}$ Epitaxial Films: Comparison Between $(hbox{La},hbox{Sr})(hbox{Al},hbox{Ta})hbox{O}_{3} $ and MgO Substrates. *IEEE Transactions on Applied Superconductivity*, **2015**, 25, 1-5	1.8	6
336	Intrinsic defects in a photovoltaic perovskite variant Cs2SnI6. *Physical Chemistry Chemical Physics*, **2015**, 17, 18900-3	3.6	148
335	Route to n-type doping in SnS. *Applied Physics Letters*, **2015**, 106, 152103	3.4	35
334	. *Journal of Display Technology*, **2015**, 11, 518-522		20
333	. *Journal of Display Technology*, **2015**, 11, 523-527		22
332	Electron Confinement in Channel Spaces for One-Dimensional Electride. *Journal of Physical Chemistry Letters*, **2015**, 6, 4966-71	6.4	46
331	Research Progress on Materials for MEMS and Electronics Devices of Electronics Materials Development Group. *Materia Japan*, **2015**, 54, 232-235	0.1	

330	Fabrication and opto-electrical properties of amorphous (Zn,B)O thin film by pulsed laser deposition. *Journal of the Ceramic Society of Japan*, **2015**, 123, 523-526	1	1
329	Effects of sulfur substitution in amorphous InGaZnO4: optical properties and first-principles calculations. *Journal of the Ceramic Society of Japan*, **2015**, 123, 537-541	1	6
328	Effects of residual hydrogen in sputtering atmosphere on structures and properties of amorphous In-Ga-Zn-O thin films. *Journal of Applied Physics*, **2015**, 118, 205703	2.5	28
327	Heteroepitaxial growth of SnSe films by pulsed laser deposition using Se-rich targets. *Journal of Applied Physics*, **2015**, 118, 205302	2.5	27
326	Detection of dead layers and defects in polycrystalline Cu2O thin-film transistors by x-ray reflectivity and photoresponse spectroscopy analyses. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2015**, 33, 051211	1.3	8
325	P-177L: Late-News Poster: Highly Efficient Inverted OLEDs using A New Transparent Amorphous Oxide Semiconductor. *Digest of Technical Papers SID International Symposium*, **2015**, 46, 1714-1716	0.5	4
324	Ligand-Hole in [SnI6] Unit and Origin of Band Gap in Photovoltaic Perovskite Variant Cs2SnI6. *Bulletin of the Chemical Society of Japan*, **2015**, 88, 1250-1255	5.1	83
323	. *Journal of Display Technology*, **2015**, 11, 720-724		10
322	Oxide TFTs **2015**, 1-28		1
321	Growth of high-quality SnS epitaxial films by H2S flow pulsed laser deposition. *Applied Physics Letters*, **2014**, 104, 072106	3.4	27
320	Positive Gate Bias Instability Induced by Diffusion of Neutral Hydrogen in Amorphous In-Ga-Zn-O Thin-Film Transistor. *IEEE Electron Device Letters*, **2014**, 35, 832-834	4.4	20
319	Two-Dimensional Transition-Metal Electride Y2C. *Chemistry of Materials*, **2014**, 26, 6638-6643	9.6	113
318	Narrow bandgap in □BaZn□As□ and its chemical origins. *Journal of the American Chemical Society*, **2014**, 136, 14959-65	16.4	25
317	Growth of c-axis-oriented superconducting KFe□As□ thin films. *ACS Applied Materials & Interfaces*, **2014**, 6, 14293-301	9.5	11
316	Epitaxial growth and electronic structure of a layered zinc pnictide semiconductor, □BaZn2As2. *Thin Solid Films*, **2014**, 559, 100-104	2.2	10
315	Fabrication and characterization of ZnS:(Cu,Al) thin film phosphors on glass substrates by pulsed laser deposition. *Thin Solid Films*, **2014**, 559, 18-22	2.2	10
314	Electric double-layer transistor using layered iron selenide Mott insulator TlFe1.6Se2. *Proceedings of the National Academy of Sciences of the United States of America*, **2014**, 111, 3979-83	11.5	26
313	. *Journal of Display Technology*, **2014**, 10, 979-983		15

312	High critical-current density with less anisotropy in BaFe2(As,P)2 epitaxial thin films: Effect of intentionally grown c-axis vortex-pinning centers. *Applied Physics Letters*, **2014**, 104, 182603	3.4	41
311	Roles of Hydrogen in Amorphous Oxide Semiconductor In-Ga-Zn-O: Comparison of Conventional and Ultra-High-Vacuum Sputtering. *ECS Journal of Solid State Science and Technology*, **2014**, 3, Q3085-Q3090	2	43
310	. *Journal of Display Technology*, **2014**, 10, 975-978		12
309	Critical factor for epitaxial growth of cobalt-doped BaFe2As2 films by pulsed laser deposition. *Applied Physics Letters*, **2014**, 104, 172602	3.4	22
308	Film Texture, Hole Transport and Field-Effect Mobility in Polycrystalline SnO Thin Films on Glass. *ECS Journal of Solid State Science and Technology*, **2014**, 3, Q3040-Q3044	2	28
307	Mobility- and temperature-dependent device model for amorphous In□Ga□ZnO thin-film transistors. *Thin Solid Films*, **2014**, 559, 40-43	2.2	30
306	Unusual pressure effects on the superconductivity of indirectly electron-doped (Ba1□Lax)Fe2As2 epitaxial films. *Physical Review B*, **2013**, 88,	3.3	16
305	Superconducting Properties and Phase Diagram of Indirectly Electron-Doped $(hbox{Sr}_{1 - x}hbox{La}_{x})hbox{Fe}_{2}hbox{As}_{2}$ Epitaxial Films Grown by Pulsed Laser Deposition. *IEEE Transactions on Applied Superconductivity*, **2013**, 23, 7300405-7300405	1.8	13
304	Surface reactivity and oxygen migration in amorphous indium-gallium-zinc oxide films annealed in humid atmosphere. *Applied Physics Letters*, **2013**, 103, 201904	3.4	26
303	Magnetic structure and electromagnetic properties of LnCrAsO with a ZrCuSiAs-type structure (Ln = La, Ce, Pr, and Nd). *Inorganic Chemistry*, **2013**, 52, 13363-8	5.1	23
302	Magnetic scattering and electron pair breaking by rare-earth-ion substitution in BaFe2As2epitaxial films. *New Journal of Physics*, **2013**, 15, 073019	2.9	18
301	Effects of Diffusion of Hydrogen and Oxygen on Electrical Properties of Amorphous Oxide Semiconductor, In-Ga-Zn-O. *ECS Journal of Solid State Science and Technology*, **2013**, 2, P5-P8	2	152
300	(Invited) Roles of Hydrogen in Amorphous Oxide Semiconductor. *ECS Transactions*, **2013**, 54, 103-113	1	70
299	Anomalous scaling behavior in a mixed-state Hall effect of a cobalt-doped BaFe2As2 epitaxial film with a high critical current density over 1 MA/cm2. *Physical Review B*, **2013**, 87,	3.3	14
298	P.3: 3-D Stacked Complementary TFT Devices using n-type □GZO and p-type F8T2 TFTs □ Operation Confirmation of NOT and NAND Logic Circuits □*Digest of Technical Papers SID International Symposium*, **2013**, 44, 995-998	0.5	1
297	4.1: Invited Paper: Electronic Structure, Carrier Transport, Defects and Impurities in Amorphous Oxide Semiconductor. *Digest of Technical Papers SID International Symposium*, **2013**, 44, 11-13	0.5	3
296	P.142L: Late-News Poster: Electron Injecting Material for OLEDs driven by Oxide TFTs: Amorphous C12A7 Electride. *Digest of Technical Papers SID International Symposium*, **2013**, 44, 1473-1476	0.5	6
295	Hydrogen passivation of electron trap in amorphous In-Ga-Zn-O thin-film transistors. *Applied Physics Letters*, **2013**, 103, 202114	3.4	92

294	Apparent high mobility ~30 cm2/Vs of amorphous InGaZnO thin-film transistor and its origin. *Journal of the Ceramic Society of Japan*, **2013**, 121, 295-298	1	4
293	Amorphous Oxide Semiconductor Thin Films. *Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan*, **2013**, 64, 392-395	0.1	
292	Microstructure and transport properties of [001]-tilt bicrystal grain boundaries in iron pnictide superconductor, cobalt-doped BaFe2As2. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2012**, 177, 515-519	3.1	32
291	Superconducting compounds with metallic square net. *Solid State Communications*, **2012**, 152, 666-670	1.6	6
290	Operation model with carrier-density dependent mobility for amorphous InGaZnO thin-film transistors. *Thin Solid Films*, **2012**, 520, 3791-3795	2.2	11
289	Effects of low-temperature ozone annealing on operation characteristics of amorphous InGaZnO thin-film transistors. *Thin Solid Films*, **2012**, 520, 3787-3790	2.2	30
288	Photovoltaic properties of n-type amorphous InGaZnO and p-type single crystal Si heterojunction solar cells: Effects of Ga content. *Thin Solid Films*, **2012**, 520, 3808-3812	2.2	18
287	Stability and high-frequency operation of amorphous InGaZnO thin-film transistors with various passivation layers. *Thin Solid Films*, **2012**, 520, 3778-3782	2.2	69
286	Amorphous InGaZnO Dual-Gate TFTs: CurrentVoltage Characteristics and Electrical Stress Instabilities. *IEEE Transactions on Electron Devices*, **2012**, 59, 1928-1935	2.9	40
285	Doping effects in amorphous oxides. *Journal of the Ceramic Society of Japan*, **2012**, 120, 447-457	1	30
284	Optical evidence for quantization in transparent amorphous oxide semiconductor superlattice. *Physical Review B*, **2012**, 86,	3.3	18
283	Band alignment of InGaZnO4/Si interface by hard x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2012**, 112, 033713	2.5	33
282	Structural relaxation in amorphous oxide semiconductor, a-In-Ga-Zn-O. *Journal of Applied Physics*, **2012**, 111, 073513	2.5	74
281	Thin Film Growth and Device Fabrication of Iron-Based Superconductors. *Journal of the Physical Society of Japan*, **2012**, 81, 011011	1.5	47
280	Maximum applied voltage detector using amorphous InGaZnO thin-film transistor exposed to ozone annealing. *Solid-State Electronics*, **2012**, 75, 74-76	1.7	4
279	Electron injection barriers between air-stable electride with low work function, C12A7:e and pentacene, C60 and copper phthalocyanine. *Journal of Materials Chemistry*, **2012**, 22, 4278		21
278	Light Irradiation History Sensor Using Amorphous In-Ga-Zn-O Thin-Film Transistor Exposed to Ozone Annealing. *IEEE Electron Device Letters*, **2012**, 33, 384-386	4.4	6
277	Role of lone pair electrons in determining the optoelectronic properties of BiCuOSe. *Physical Review B*, **2012**, 85,	3.3	37

276	Thin film growth by pulsed laser deposition and properties of 122-type iron-based superconductor AE(Fe1−xCox)2As2(AE=alkaline earth). *Superconductor Science and Technology*, **2012**, 25, 084015	3.1	41
275	Metal-Semiconductor Field-Effect Transistor Made Using Amorphous In-Ga-Zn-O Channel and Bottom Pt Schottky Contact Structure at 200°C. *ECS Solid State Letters*, **2012**, 1, Q8-Q10		19
274	Identical effects of indirect and direct electron doping of superconducting BaFe2As2 thin films. *Physical Review B*, **2012**, 85,	3.3	41
273	Amorphous In-Ga-Zn-O Thin Film Transistors: Fabrication and Properties **2012**, 485-536		3
272	Highly stable amorphous In-Ga-Zn-O thin-film transistors produced by eliminating deep subgap defects. *Applied Physics Letters*, **2011**, 99, 053505	3.4	139
271	Effects of excess oxygen on operation characteristics of amorphous In-Ga-Zn-O thin-film transistors. *Applied Physics Letters*, **2011**, 99, 093507	3.4	166
270	Bipolar Conduction in SnO Thin Films. *Electrochemical and Solid-State Letters*, **2011**, 14, H13		132
269	Advantageous grain boundaries in iron pnictide superconductors. *Nature Communications*, **2011**, 2, 409	17.4	212
268	A germanate transparent conductive oxide. *Nature Communications*, **2011**, 2, 470	17.4	75
267	35.5L: Late-News Paper: An Ambipolar Oxide TFT. *Digest of Technical Papers SID International Symposium*, **2011**, 42, 486-487	0.5	1
266	Microbeam complex at TIARA: Technologies to meet a wide range of applications. *Nuclear Instruments & Methods in Physics Research B*, **2011**, 269, 2184-2188	1.2	14
265	Simple Analytical Model of On Operation of Amorphous InGaZnO Thin-Film Transistors. *IEEE Transactions on Electron Devices*, **2011**, 58, 3463-3471	2.9	47
264	Solid-phase epitaxial growth of (111)-oriented Si film on InGaO3(ZnO)5 buffer layer. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 920-923	2.1	
263	Excimer laser crystallization of InGaZnO4 on SiO2 substrate. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 1694-1696	2.1	6
262	Ambipolar oxide thin-film transistor. *Advanced Materials*, **2011**, 23, 3431-4	24	207
261	LaCo2B2: a Co-based layered superconductor with a ThCr2Si2-type structure. *Physical Review Letters*, **2011**, 106, 237001	7.4	29
260	. *IEEE Electron Device Letters*, **2011**, 32, 1695-1697	4.4	69
259	Depth analysis of subgap electronic states in amorphous oxide semiconductor, a-In-Ga-Zn-O, studied by hard x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2011**, 109, 073726	2.5	141

258	Biaxially textured cobalt-doped BaFe2As2 films with high critical current density over 1 MA/cm2 on MgO-buffered metal-tape flexible substrates. *Applied Physics Letters*, **2011**, 98, 242510	3.4	105
257	New functionalities in abundant element oxides: ubiquitous element strategy. *Science and Technology of Advanced Materials*, **2011**, 12, 034303	7.1	30
256	Electronic Structure and Photovoltaic Properties of n-Type Amorphous In-Ga-Zn-O and p-Type Single Crystal Si Heterojunctions. *Electrochemical and Solid-State Letters*, **2011**, 14, H346		10
255	INCREASING ANTITUMOR EFFECTS OF CHEMORADIOTHERAPY BY DRUG EFFLUX INHIBITION WITH ENCAPSULATED ANTI-RLIP-76. *International Journal of PIXE*, **2011**, 21, 39-46	0.1	4
254	Operation Characteristics of Thin-Film Transistors Using Very Thin Amorphous InGaZnO Channels. *Electrochemical and Solid-State Letters*, **2011**, 14, H197		43
253	Josephson junction in cobalt-doped BaFe2As2 epitaxial thin films on (La,Sr)(Al,Ta)O3 bicrystal substrates. *Applied Physics Letters*, **2010**, 96, 142507	3.4	66
252	DC superconducting quantum interference devices fabricated using bicrystal grain boundary junctions in Co-doped BaFe2As2epitaxial films. *Superconductor Science and Technology*, **2010**, 23, 082001	3.1	46
251	Large Photoresponse in Amorphous InGaZnO and Origin of Reversible and Slow Decay. *Electrochemical and Solid-State Letters*, **2010**, 13, H324		54
250	Sputtering formation of p-type SnO thin-film transistors on glass toward oxide complimentary circuits. *Applied Physics Letters*, **2010**, 97, 072111	3.4	165
249	Three-dimensionally stacked flexible integrated circuit: Amorphous oxide/polymer hybrid complementary inverter using n-type a-InGaZnO and p-type poly-(9,9-dioctylfluorene-co-bithiophene) thin-film transistors. *Applied Physics Letters*, **2010**, 96, 263509	3.4	81
248	Intrinsic carrier mobility in amorphous InGaZnO thin-film transistors determined by combined field-effect technique. *Applied Physics Letters*, **2010**, 96, 262105	3.4	48
247	Origins of hole doping and relevant optoelectronic properties of wide gap p-type semiconductor, LaCuOSe. *Journal of the American Chemical Society*, **2010**, 132, 15060-7	16.4	36
246	Present status of amorphous In-Ga-Zn-O thin-film transistors. *Science and Technology of Advanced Materials*, **2010**, 11, 044305	7.1	1287
245	Fabrication of Atomically Flat ScAlMgO4 Epitaxial Buffer Layer and Low-Temperature Growth of High-Mobility ZnO Films. *Crystal Growth and Design*, **2010**, 10, 1084-1089	3.5	5
244	Material characteristics and applications of transparent amorphous oxide semiconductors. *NPG Asia Materials*, **2010**, 2, 15-22	10.3	664
243	Origin of definite Hall voltage and positive slope in mobility-donor density relation in disordered oxide semiconductors. *Applied Physics Letters*, **2010**, 96, 122103	3.4	121
242	High Critical Current Density 4 MA/cm2in Co-Doped BaFe2As2Epitaxial Films Grown on (La,Sr)(Al,Ta)O3Substrates without Buffer Layers. *Applied Physics Express*, **2010**, 3, 063101	2.4	81
241	Fabrication and electron transport properties of epitaxial films of electron-doped 12CaO7Al2O3 and 12SrO7Al2O3. *Journal of Solid State Chemistry*, **2010**, 183, 385-391	3.3	17

240	Electrical and magnetic properties of quaternary compounds LnMnPO (Ln=Nd, Sm, Gd) with ZrCuSiAs-type structure. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2010**, 173, 47-50	3.1	7
239	Short-channel nanowire transistor using a nanoporous crystal semiconductor 12CaO□7Al2O3. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2010**, 173, 37-40	3.1	11
238	Impurities in FeAs-based superconductor, SrFe2As2, studied by first-principles calculations. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2010**, 173, 244-247	3.1	4
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